

isc Silicon NPN Power Transistor

2SC3252

DESCRIPTION

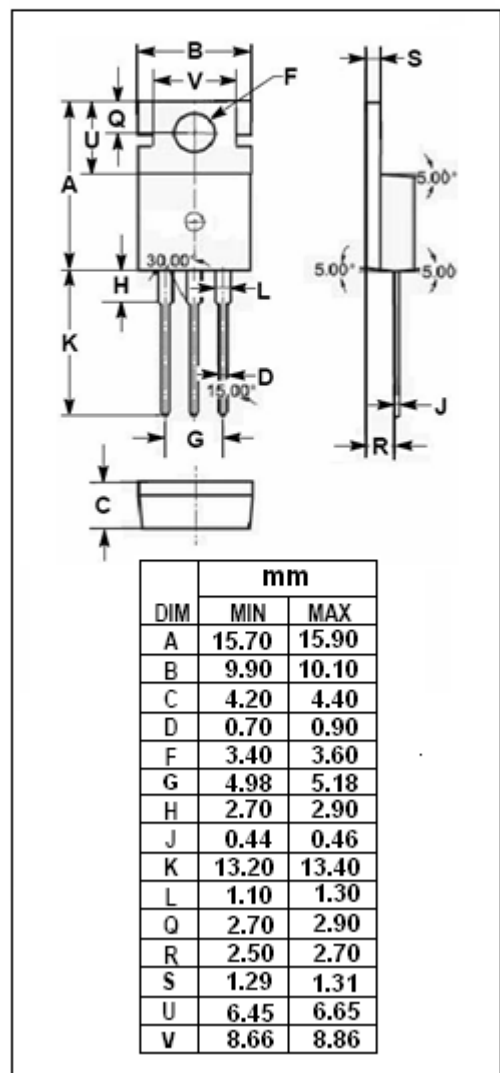
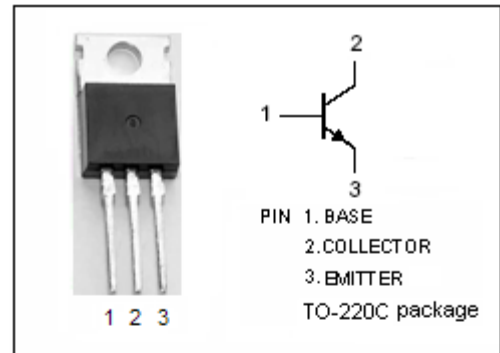
- Low Collector Saturation Voltage
- Good Linearity of  $h_{FE}$
- High Switching Speed
- Complement to Type 2SA1288

APPLICATIONS

- Various inductance lamp drivers for electrical equipment
- Inverters, converters
- Power amplifier
- Switching regulator, driver

ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	80	V
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	3	A
$I_{CM}$	Collector Current-Pulse	5	A
$P_C$	Collector Power Dissipation @ $T_C=25^{\circ}C$	30	W
$T_J$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-55~150	$^{\circ}C$



**isc Silicon NPN Power Transistor****2SC3252****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=1\text{mA}; R_{BE}=\infty$	60			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}; I_E=0$	80			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}; I_C=0$	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=1.5\text{A}; I_B=75\text{mA}$			0.4	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=40\text{V}; I_E=0$			100	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=4\text{V}; I_C=0$			100	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C=1\text{A}; V_{CE}=2\text{V}$	70		280	
$f_T$	Current-Gain—Bandwidth Product	$I_C=1\text{A}; V_{CE}=5\text{V}$		100		MHz

◆  **$h_{FE}$  Classifications**

Q	R	S
70-140	100-200	140-280